L Number	Hits	Search Text	DB	Time stamp
-	397252	349/$6 or (liquid near3 crystal) or lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	13818	substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:08
-	13818	(349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:09
-	12585	((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:09
-	7493	busbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:10
-	9150	storage near4 capacita$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:09
-	1	((((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))) and electrode) and busbar) and (storage near4 capacita$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:10
-	10	(((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))) and electrode) and busbar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:10
-	604	busbar and narrow$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:11
-	186	busbar same narrow$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:33
-	2	(busbar same narrow$3) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:12
-	8	(349/$6 or (liquid near3 crystal) or lcd) and (busbar same narrow$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:30

-	444	busbar same (narrow$3 or thin$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:33
-	20	(349/$6 or (liquid near3 crystal) or lcd) and (busbar same (narrow$3 or thin$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 19:33
-	9	((349/$6 or (liquid near3 crystal) or lcd) and (busbar same (narrow$3 or thin$4))) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/11/16 20:08
-	4	(6028650, "6317182").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:08
-	1208	((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))) and (storage near4 capacita$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:09
-	16635	busbar or (storage near4 capacita$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:09
-	1231	(busbar or (storage near4 capacita$6)) and ((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:10
-	395	(storage near4 capacita$6) near9 (thin$3 or narrow$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:10
-	210	((storage near4 capacita$6) near9 (thin$3 or narrow$3)) and ((349/$6 or (liquid near3 crystal) or lcd) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	726	349/38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	252	349/37	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	726	349/38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32

-	505	349/39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	2055	349/139	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	3075	349/37 or 349/38 or 349/39 or 349/139	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	582	(349/37 or 349/38 or 349/39 or 349/139) and narrow$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:32
-	71	(349/37 or 349/38 or 349/39 or 349/139) and ((capacit$5 or bus) near9 narrow$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:45
-	46	(349/37 or 349/38 or 349/39 or 349/139) and ((capacit$5) near9 narrow$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:33
-	61	((349/37 or 349/38 or 349/39 or 349/139) and ((capacit$5 or bus) near9 narrow$3)) and (substrate and (liquid near3 crystal) and pixel and (scan$4 or gate) and (data or signal$3) and (switch$3 or tft or transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:34
-	7	(349/37 or 349/38 or 349/39 or 349/139) and ((capacit$5 and bus) near9 narrow$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/16 20:45
-	808	349/38	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	574	349/39	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	264	349/37	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	2181	349/139	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54

-	825	349/141	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	428	349/142	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	4126	349/38 or 349/39 or 349/37 or 349/139 or 349/141 or 349/142	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:54
-	2	(349/38 or 349/39 or 349/37 or 349/139 or 349/141 or 349/142) and substrate and (pixel near3 electrode) and (scan$4 or gate) and (switch$4 or ((thin near3 film) or tft)) and (counter near3 electrode) and (busbar)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:56
-	269	(349/38 or 349/39 or 349/37 or 349/139 or 349/141 or 349/142) and substrate and (pixel near3 electrode) and (scan$4 or gate) and (switch$4 or ((thin near3 film) or tft)) and (counter near3 electrode) and (busbar or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:56
-	161	(349/38 or 349/39 or 349/37 or 349/139 or 349/141 or 349/142) and substrate and (pixel near3 electrode) and (scan$4 or gate) and (switch$4 or ((thin near3 film) or tft)) and (counter near3 electrode) and (busbar or capacitor) and overlap$4 and shape	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:58
-	4	(6028650, "6317182").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:59